## Structural and Electronic Properties of $CdSe_xTe_{1-x}$ /CdTe thin-film photovoltaic devices: Carrier Dynamics Analysis by Charge Carrier Collection Efficiency

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> 100 50 QE charge collection of CdSeTe/CdTe devices: 28.66 mA/cm<sup>2</sup> 0 400 600 800

Fig. 1. Quantum charge carrier efficiency measurements. The total charge carrier collection by QE is 28.66 mA/cm<sup>2</sup>. The blue line is data for CdSe<sub>x</sub>Te<sub>1-x</sub>/CdTe devices and the red line is for bandgap energy calculations. The bandgap energy is calculated as 1.41 eV.